

IRF634

N-channel mosfet transistor



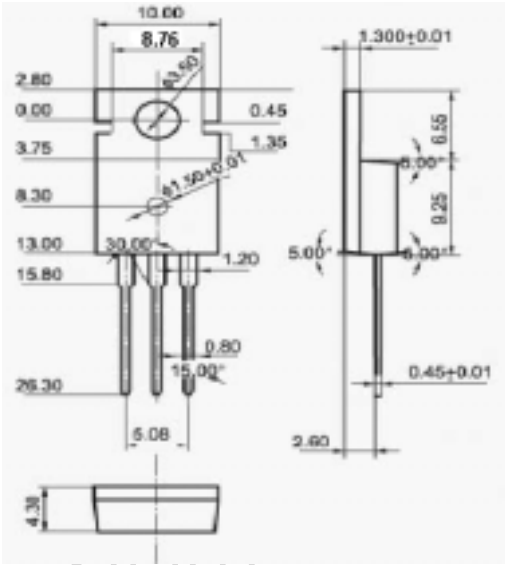
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◆ Features

- With TO-220 package
- Simple drive requirements
- Fast switching
- $V_{DSS}=250V$ ;  $R_{DS(ON)} \leq 0.45 \Omega$ ;  $I_D=8.1A$
- 1.gate 2.drain 3.source

◆ Absolute Maximum Ratings  $T_c=25$

| SYMBOL    | PARAMETER                           | RATING   | UNIT |
|-----------|-------------------------------------|----------|------|
| $V_{DSS}$ | Drain-source voltage ( $V_{GS}=0$ ) | 250      | V    |
| $V_{GS}$  | Gate-source voltage                 | $\pm 20$ | V    |
| $I_D$     | Drain Current-continuous@ $T_c=25$  | 8.1      | A    |
| $P_{tot}$ | Total Dissipation@ $T_c=25$         | 74       | W    |
| $T_j$     | Max. Operating Junction temperature | 150      |      |
| $T_{stg}$ | Storage temperature                 | -65~150  |      |



TO-220

◆ Electrical Characteristics  $T_c=25$

| SYMBOL        | PARAMETER                        | CONDITIONS                     | MIN | MAX       | UNIT       |
|---------------|----------------------------------|--------------------------------|-----|-----------|------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage   | $V_{GS}=0$ ; $I_D=0.25mA$      | 250 |           | V          |
| $V_{GS(TH)}$  | Gate threshold voltage           | $V_{DS}=V_{GS}$ ; $I_D=0.25mA$ | 2   | 4         | V          |
| $R_{DS(ON)}$  | Drain-source on-stage resistance | $V_{GS}=10V$ ; $I_D=5.1A$      |     | 450       | m $\Omega$ |
| $I_{GSS}$     | Gate source leakage current      | $V_{GS}=\pm 20V$ ; $V_{DS}=0$  |     | $\pm 100$ | nA         |
| $I_{DSS}$     | Zero gate voltage drain current  | $V_{DS}=250V$ ; $V_{GS}=0$     |     | 25        | $\mu A$    |
| $V_{SD}$      | Diode forward voltage            | $I_F=8.1A$ ; $V_{GS}=0$        |     | 2.0       | V          |